

“Origin of the performances degradation of two-dimensional-based metal-oxide semiconductor field effect transistors in the sub-10 nm regime: A first-principles study”. Lu AKA, Pourtois G, Agarwal T, Afzalian A, Radu IP, Houssa M, Applied physics letters **108**, 043504 (2016). <http://doi.org/10.1063/1.4940685>